

ABSTRACT

A method for manufacturing a semiconductor device is disclosed. The method for manufacturing a semiconductor device includes providing a laminate including a dicing/die-bonding integrated film including a dicing film (film A) having a base film and a pressure-sensitive adhesive layer provided on the base film, and a die-bonding film (film B) provided on the pressure-sensitive adhesive layer, and a plurality of semiconductor chips provided on the film B of the integrated film, the plurality of semiconductor chips being obtained by singulating a semiconductor wafer; and producing a semiconductor chip with a film B piece by expanding the film A of the laminate under cooling conditions to singulate the film B, thereby obtaining the semiconductor chip and a film B piece resulting from the singulation of the film B. A tensile stress of the film A at 20% elongation at -15°C in a tensile test is 15 MPa or more, and an elongation at break of the film A at -15°C in the tensile test is 500% or less.

No Suitable Figure.